

Page 16, delete whole paragraph starting in line 18 and replace it with the following new paragraph:

Ba
Fig. 6 shows the structure of the Light-emitting device 20. The Light-emitting device 20 is a light-emitting diode composed of a substrate 21, a buffer layer 22, an n-type GaN layer 23, an active layer 24, a p-type semiconductor layer 25, a negative electrode 26, and a positive electrode 27. The specifications of these members are tabulated below.

IN THE CLAIMS

Please amend claims 14, 19 and 21 as follows:

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14. (Amended) A semiconductor light-emitting apparatus of flip chip bonding type, comprising:

a transparent base made of an inorganic material, which has on one side thereof a first bonding pad and a second bonding pad to be connected to a pair of lead frames with a space between the first and the second bonding pads where a semiconductor light-emitting element is fixed, the light-emitting element including a positive electrode that covers substantially an entire surface of a light-emitting layer of the light-emitting element, and the positive electrode reflecting light emitted from the light-emitting layer toward the light-emitting layer.

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19. (Amended) A pair of lead frames for use in a light-emitting apparatus of flip chip bonding type comprising:

a transparent base having on a first surface thereof a first and a second bonding pad and

a GaN semiconductor light-emitting device fixed on the first surface thereof, wherein a first lead frame has a first mount which faces the dominant light emitting direction of the light-emitting apparatus and on which the first bonding pad is to be

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fixed, and a second lead frame has a second mount which faces the dominant light emitting direction and on which the second bonding pad is to be fixed, the light-emitting device including a positive electrode that covers substantially an entire surface of a light-emitting layer of the light-emitting device, and the positive electrode reflecting light emitted from the light-emitting layer toward the light-emitting layer.

21. (Amended) A light-emitting diode comprising:

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a sapphire substrate;

a light emitting layer made of GaN semiconductor and formed on said sapphire substrate; and

a positive electrode formed on said light emitting layer;

wherein said positive electrode is supplied with electricity through a wire, reflects light from said light emitting layer toward said sapphire substrate and covers substantially an entire surface of the light emitting layer.